

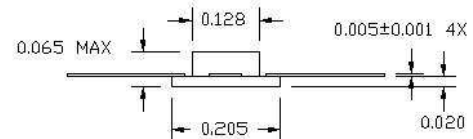
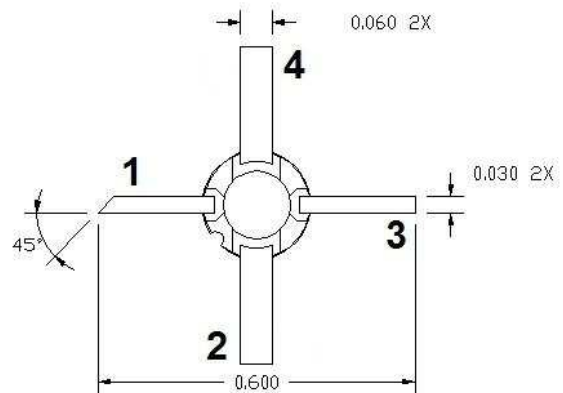
## HIGH FREQUENCY LINEAR POWER TRANSISTOR

### Description

The KX102-27 is a high performance NPN silicon bipolar transistor that is designed to be a replacement for the AT64020 Transistor. This device is designed for use in medium power, wide band amplifier and oscillator applications over microwave frequencies. Packaged in a high-conductivity hermetically sealed package, this transistor well suited for high reliability applications.

### Features

- High Output Power:
  - 27.5 dBm typical P1dB at 2.0 GHz
  - 26.5 dBm typical P1dB at 4.0 GHz
- High Gain at 1dB Compression: 12.5 dB typical at 2.0 GHz
- 9.5 dB typical G1dB at 4.0 GHz
- 35% Total Efficiency



### Absolute Maximum Rating ( +25°C )

Parameter	Symbol	Rating	Units
Collector to Base Voltage	$V_{CBO}$	40	V
Collector to Emitter Voltage	$V_{CEO}$	20	V
Emitter to Base Voltage	$V_{EBO}$	2.0	V
Collector Current	$I_C$	200	mA
Power Dissipation	$P_T$	3	W
Junction Temperature	$T_J$	200	°C
Storage Temperature	$T_{STG}$	-65 to +200	°C

### Pinout

1	Base
2	Emitter
3	Collector
4	Emitter

### Electrical Characteristics ( +25°C )

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Insertion Power Gain	$ S_{21E} ^2$	$V_{CE} = 16\text{ V}, I_C = 110\text{ mA}, f = 2\text{ GHz}$		7		dB
Power Output @ 1dB Gain Compression	$P_{1dB}$	$V_{CE} = 16\text{ V}, I_C = 110\text{ mA}, f = 2\text{ GHz}$	26.5	27.5		dBm
1dB Compressed Gain	$G_{1dB}$	$V_{CE} = 16\text{ V}, I_C = 110\text{ mA}, f = 2\text{ GHz}$	8.5	10		dB
Total Efficiency at P1dB	$\eta_T$	$V_{CE} = 16\text{ V}, I_C = 20\text{ mA}, f = 4\text{ GHz}$		35		%
Forward Current Transfer Ratio	$h_{FE}$	$V_{CE} = 8\text{ V}, I_C = 110\text{ mA}$	20	50	200	
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 16\text{ V}, I_E = 0\text{ mA}$			1.0	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 1\text{ V}, I_C = 0\text{ mA}$			1.0	$\mu\text{A}$
Thermal Resistance	$\Theta_{JC}$			40		°C/W

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### Typical Performance Curves ( +25°C )

Typical performance curves currently being evaluated. Contact KCB Solutions for further Information.

### MIL-PRF-19500 Screening Flow

Test Inspection	MIL-STD-750 Method	Condition	JANS	JANTXV	JANTX
Internal Visual Inspection	2070	B	100%	100%	100%
Temperature Cycling	1051	20 cycles	100%	100%	100%
Thermal Impedance	3131		100%	100%	100%
Constant Acceleration	2006	Y1 direction	100%	NA	NA
PIND	2052	A ( 5 Cycles)	100%	NA	NA
Seal: Fine Leak	1071	A	100%	100%	100%
Gross Leak		C	100%	100%	100%
Serialization	Per Product Specification		100%	NA	NA
Initial Electrical Test	Per Product Specification	+25°C	100%	NA	NA
High Temp Reverse Bias	1039	A	100%	100%	100%
Interim Electrical Test	Per Product Specification	+25°C	100%	100%	100%
Power Burn In	1039	B	100%	100%	100%
			240 hrs min	160 hrs min	160 hrs min
Final Electrical	Per Product Specification	+25°C	100%	100%	100%
PDA Calculation	Per Product Specification		100%	100%	100%
Seal: Fine Leak	1071	A	100%	100%	100%
Gross Leak		C	100%	100%	100%
Radiography	2076		100%	NA	NA
External Visual	2071		100%	NA	NA
Case Isolation	1081		100%	100%	100%

### Ordering Information

KCB Solutions Part Number	Screening Level
KX102-27	Unscreened
KX102-27V	JANTXV Screening
KX102-27X	JANTX Screening
KX102-27S	JANS Screening